a first wiring layer provided between the selection circuit and the digital circuit;

a second wiring layer provided between the selection circuit and the analog circuit; and

a voltage providing means coupled to the first wiring layer and for providing a voltage to the first wiring layer when the first wiring layer is electrically cut from the external terminal by the selection circuit.

12. A semiconductor integrated circuit according to claim 11, wherein the digital circuit has a first voltage terminal for receiving the voltage and the analog circuit has a second voltage terminal for receiving the voltage, wherein the voltage providing means includes a first switching circuit coupled between the first wiring layer and the first voltage terminal and a second switching circuit coupled between the first wiring layer and the second voltage terminal, and wherein the connection node between the second switching circuit and the first wiring layer is located between the selection circuit and the connection node between the first switching circuit and the first wiring layer.

13. A semiconductor integrated circuit according to claim 12, wherein the digital circuit is formed in a semiconductor region which is formed on the semiconductor substrate via an insulation layer, and wherein the analog circuit is formed in a semiconductor region which is formed on the semiconductor substrate via an insulation layer.

14. A semiconductor integrated circuit according to claim 12, wherein each of the first wiring layer and the second wiring layer is formed on the semiconductor substrate.

15. A semiconductor integrated circuit comprising:

a transmitting circuit including a modulation circuit for modulating a signal;

a control circuit coupled to the transmitting circuit and controlling the transmitting circuit;

a test circuit coupled the control circuit;

an external terminal being capable of transmitting a signal to be transmitted to the transmitting circuit;

a first switching circuit coupled between the external terminal and a wiring layer which is coupled to the test circuit; and

a voltage providing circuit coupled to the wiring layer and providing a voltage to the wiring layer when the wiring layer is electrically cut from the external terminal.

16. A semiconductor integrated circuit according to claim 15, wherein each of the transmitting circuit, the control circuit, the test circuit and the wiring layer is formed on a semiconductor substrate.

17. A semiconductor integrated circuit according to claim 16, further comprising a second switching circuit coupled between the external terminal and the transmitting circuit.

18. A semiconductor integrated circuit according to claim 16, wherein the voltage providing circuit includes a third switching circuit coupled between the wiring layer and the voltage to be supplied to the transmitting circuit and a fourth switching circuit coupled between the wiring layer and the voltage to be supplied to the test circuit, and wherein the fourth switching circuit is located between the third switching circuit and the test circuit.

19. A semiconductor integrated circuit according to claim 18, further comprising a second switching circuit coupled between the external terminal and the transmitting circuit.